ETCHING METHOD AND PLASMA PROCESSING SYSTEM

ABSTRACT

An etching method includes: (a) providing a substrate having a silicon-containing film and a mask on the silicon-containing film in a chamber of a plasma processing apparatus, and (b) etching the silicon-containing film by generating plasma from a processing gas containing HF gas, and PCl_aF_b gas (each of a and b is an integer of 1 or more) or $PC_cH_dF_e$ gas (c is an integer of 0 or more, and each of d and e is an integer of 1 or more), in the chamber.

[Figure 2]